

<b>SANYO</b>	No.856F	<b>2SK303</b>
		N-Channel Junction Silicon FET Low-Frequency General-Purpose Amp Applications

**Features**

- Ideal for potentiometers, analog switches, low frequency amplifiers, constant current supplies, and impedance conversion.

**Absolute Maximum Ratings at Ta = 25°C**

			unit
Drain to Source Voltage	V <sub>DS</sub>	30	V
Gate to Drain Voltage	V <sub>GDS</sub>	-30	V
Gate Current	I <sub>G</sub>	10	mA
Drain Current	I <sub>D</sub>	20	mA
Allowable Power Dissipation	P <sub>D</sub>	200	mW
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

**Electrical Characteristics at Ta = 25°C**

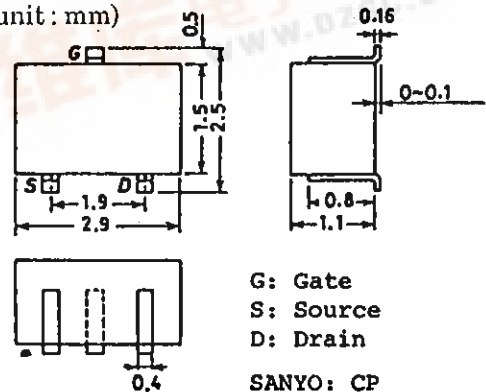
			min	typ	max	unit
Gate to Drain	V <sub>(BR)GDS</sub>	I <sub>G</sub> = -10μA	-30			V
Gate Cutoff Current	I <sub>GSS</sub>	V <sub>GS</sub> = -20V			-1.0	nA
Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0	0.6*		12.0*	mA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1μA		-1	-4	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0, f = 1MHz	2.5	6.0		mS
Input Capacitance	c <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0, f = 1MHz		5		pF
Output Capacitance	c <sub>rss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0, f = 1MHz		1.5		pF
Drain to Source ON Resistance	R <sub>DS(ON)</sub>	V <sub>DS</sub> = 10mV, V <sub>GS</sub> = 0		250		Ω

\* The 2SK303 is classified by I<sub>DSS</sub> as follows (unit : mA)

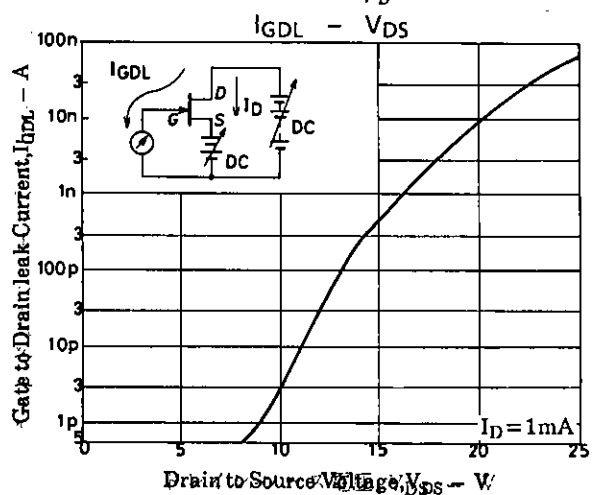
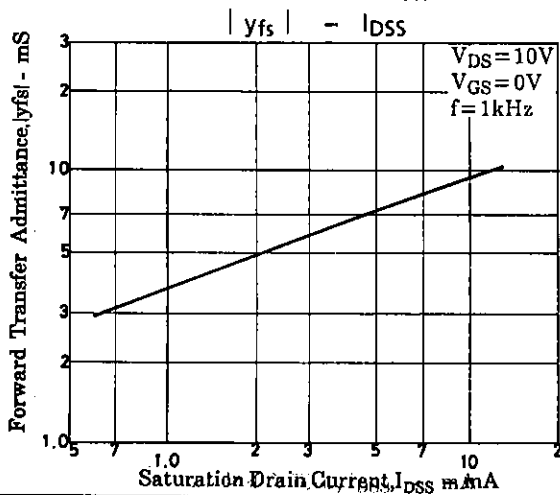
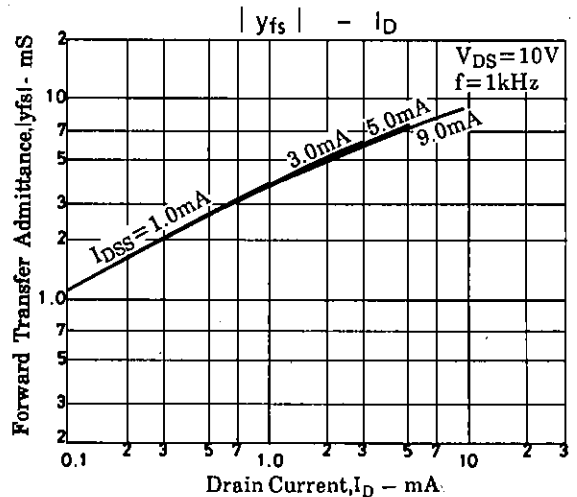
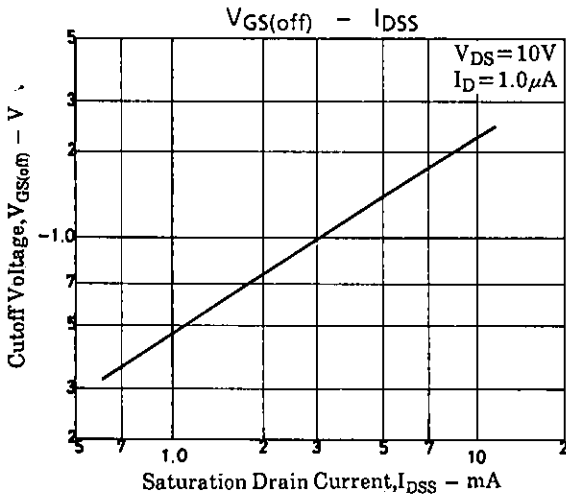
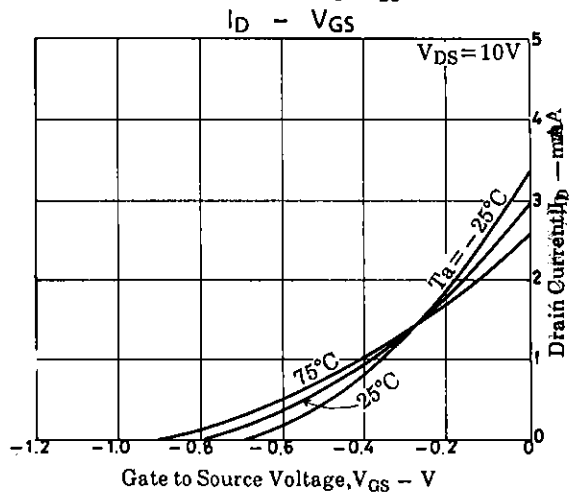
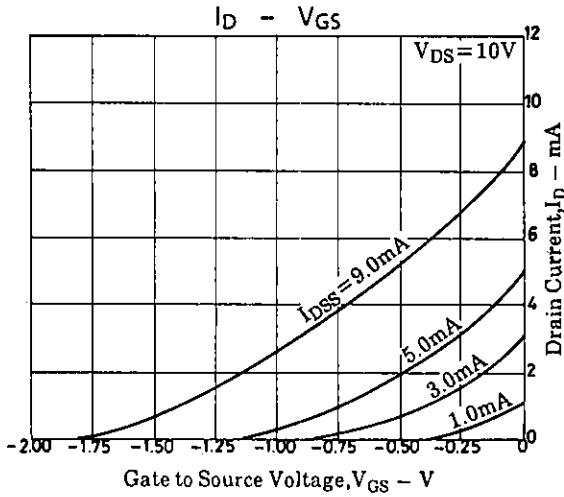
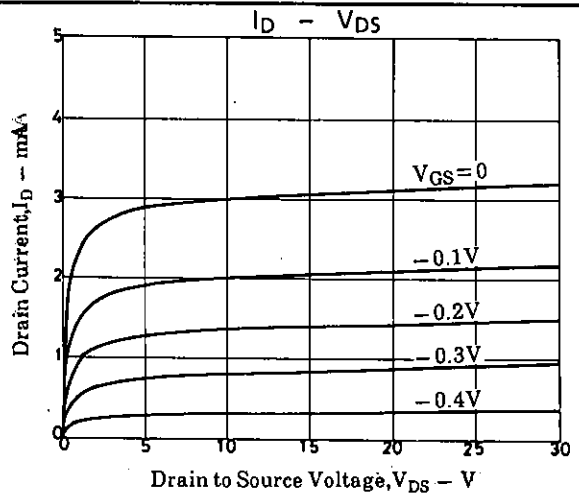
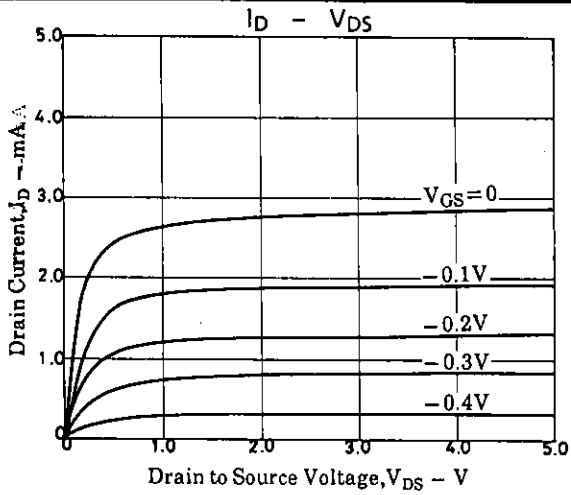
0.6	2	1.5	1.2	3	3.0	2.5	4	6.0	5.0	5	12.0
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Note Marking : V  
I<sub>DSS</sub> rank : 2, 3, 4, 5

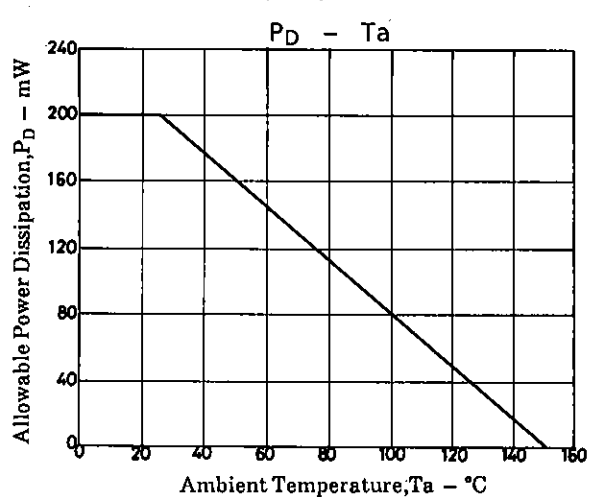
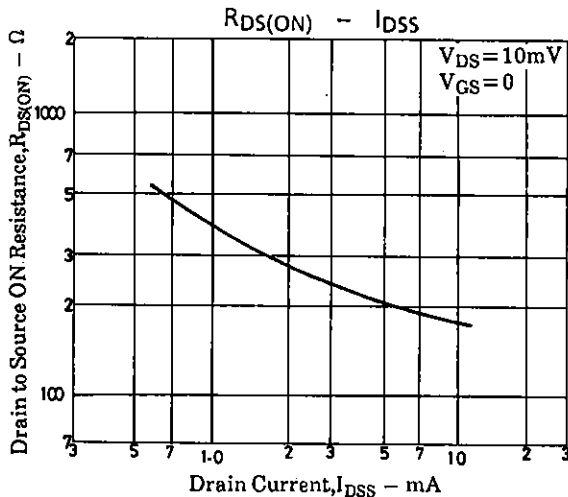
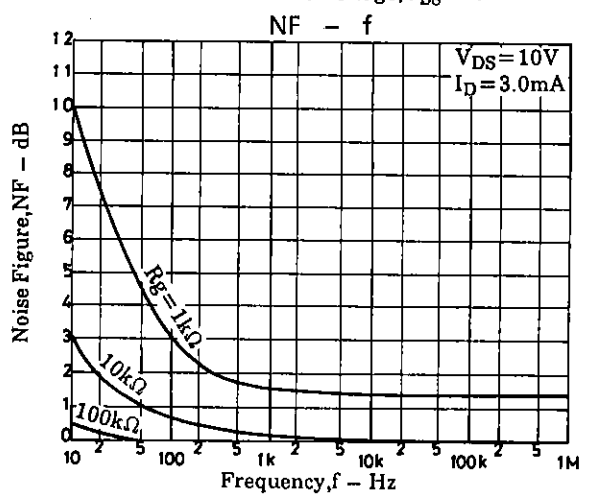
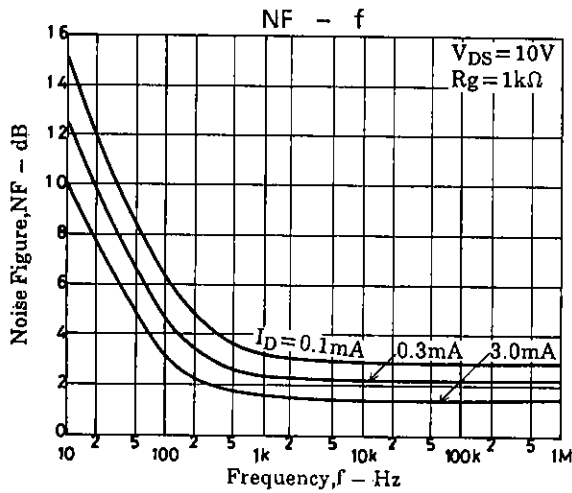
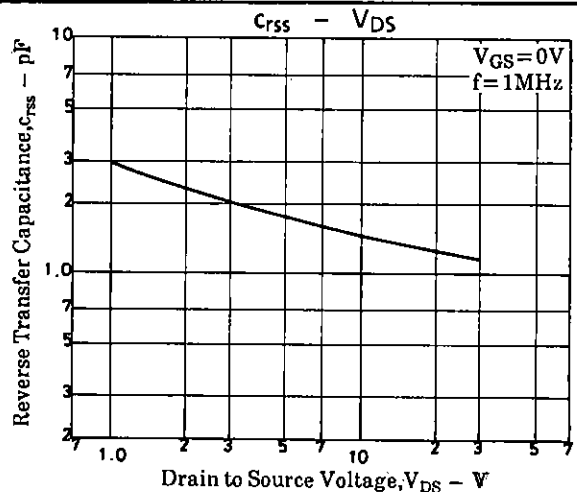
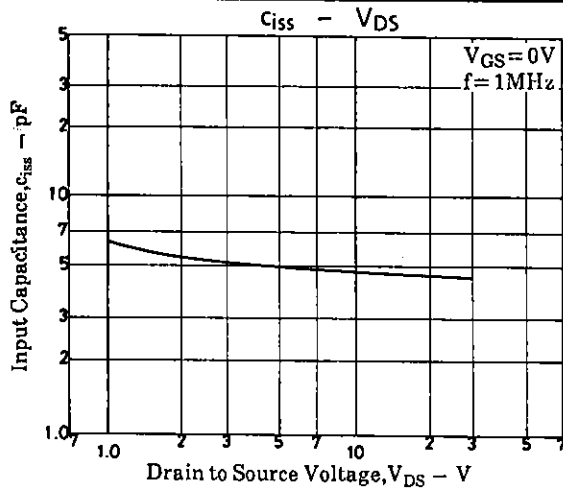
**Package Dimensions 2050**  
(unit : mm)



# 2SK303



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